



PRODUCT NAME : 2SA950 PNP General Purpose Transistor (Pack of 5)

PRICE : Rs 39.00

SKU : RM2113



NOTE: THE PRODUCT MAY BE DIFFERENT FROM IMAGE SHOWN ABOVE. Copyrights by Robomart.com

DESCRIPTION

Features

- Collector-Emitter Volt (V_{ce0}): 30V
- Collector-Base Volt (V_{cb0}): 35V
- Collector Current (I_c): 0.8A
- h_{fe} : 100-320 @ 100mA
- Power Dissipation (P_{tot}): 600mW
- Current-Gain-Bandwidth (f_{total}): 120MHz
- Type: PNP

TOSHIBA

2SA950

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA950

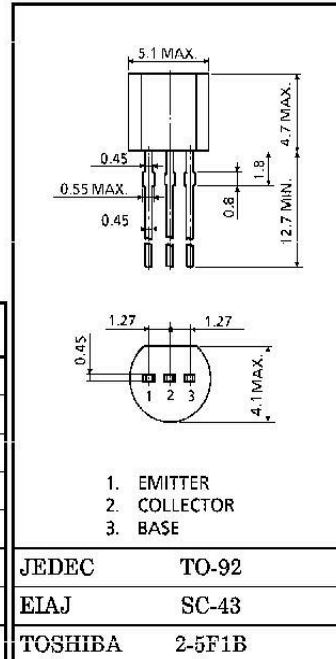
AUDIO POWER AMPLIFIER APPLICATIONS

Unit in mm

- High h_{FE} : $h_{FE}=100\sim320$
- 1W Output Applications
- Complementary to 2SC2120

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Weight : 0.21g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$	—	—	-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-30	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -700\text{mA}$	35	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -20\text{mA}$	—	—	-0.7	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1\text{V}, I_C = -10\text{mA}$	-0.5	—	-0.8	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0,$ $f = 1\text{MHz}$	—	19	—	pF

Note : $h_{FE(1)}$ Classification O : 100~200, Y : 160~320

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1996-09-02 1/2

